

	Type	Hi ts	Search Text	DBs	Time Stamp	Com ments	E rror s
1	BRS	31	(process\$6 or react\$6) near chamber and vacuum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:09		0
2	BRS	20	(process\$6 or react\$6) near chamber and vacuum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6 and (hf or nh3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/25 00:39		0
3	IS&R	2	("5344522").PN	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/26 03:13		0
4	BRS	31	(process\$6 or react\$6) near chamber and vacuum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/25 00:32		0

Type	Hi ts	Search Text	DBs	Time Stamp	Com ments	Cor ror	E rror
5	BRS0	chemical near treat\$6 near chamber and vacuum and temperature and control\$6 and gas and (substrate or wafer) with hold\$6 and heat\$6 and (hf or nh3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/25 00:41		0	
6	BRS13	treat\$6 and chamber and vacuum and temperature and control\$6 and gas and (substrate or wafer) with hold\$6 and heat\$6 and (hf or nh3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/25 00:42		0	
7	BRS20	wafer with chamber and vacuum and temperature and control\$6 and gas and (substrate or wafer) with hold\$6 and heat\$6 and (hf or nh3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/25 00:42		0	

			Type Hi ts	Search Text	DBs	Time Stamp	Com men ts	Cor re fie d	Err or ors
8	BRS	0		(process\$6 or react\$6) and wash\$6 near chamber and vacuum and temperature and gas and (substrate or wafer) near hold\$6 near heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:11		0	
9	BRS	0		wash\$6 near chamber and vacuum and temperature and gas and (substrate or wafer) near hold\$6 near heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:12		0	
10	BRS	0		wash\$6 and chamber and vacuum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6 with temperature with control\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:13		0	
11	IS& R	2		("5344522") .PN .	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/26 03:13		0	
12	BRS	39		chamber and vacuum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 08:06		0	

	Type	Hi ts	Search Text	DBs	Time Stamp	Comments	Corr or	Corr or
13	BRS	2	wash\$6 and chamber and vacuum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:18		0	
14	BRS	26	(wash\$6 or clean\$6) with (wafer or substrate) and chamber and vacuum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 08:04		0	
15	IS&R	2	("5254505").PN	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/26 08:04		0	
16	BRS	39	chamber and vacuum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 08:08		0	
17	BRS	2	loadlock near chamber and vacuum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 08:08		0	